

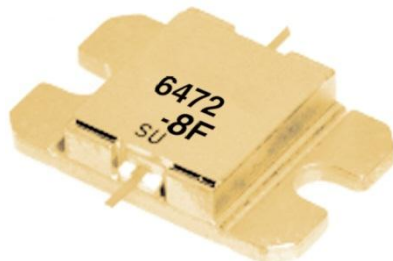
FEATURES

- High Output Power: $P_{1dB} = 39.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.5\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 36\%$ (Typ.)
- Low IM3 = $-46\text{dBc}@P_o = 28.5\text{dBm}$
- Broad Band: 6.4 to 7.2GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$
- Hermetically Sealed Package

DESCRIPTION

The FLM6472-8F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATING (Case Temperature $T_c=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	42.8	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -4.4 mA respectively with gate resistance of 100ohm.

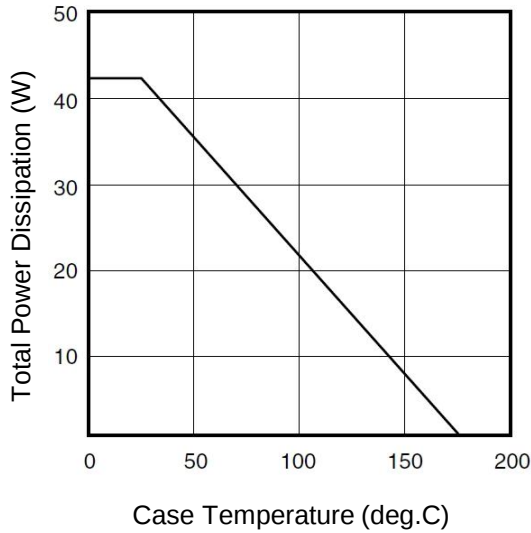
ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	3400	5200	mA
Transconductance	g_m	$V_{DS}=5V, I_{DS}=2200\text{mA}$	-	3400	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=170\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-170\text{uA}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$ $I_{DS}=0.65 I_{DSS}$ (Typ.), $f=6.4$ to 7.2 GHz, $Z_S=Z_L=50\text{ohm}$	38.5	39.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.5	9.5	-	dB
Drain Current	I_{DSr}		-	2200	2600	mA
Power-added Efficiency	η_{add}		-	36	-	%
Gain Flatness	ΔG		-	-	1.2	dB
3rd Order Intermodulation Distortion	IM_3	$f = 7.2$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 28.5\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	3.0	3.5	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{DSr} \times R_{th}$	-	-	80	deg.C

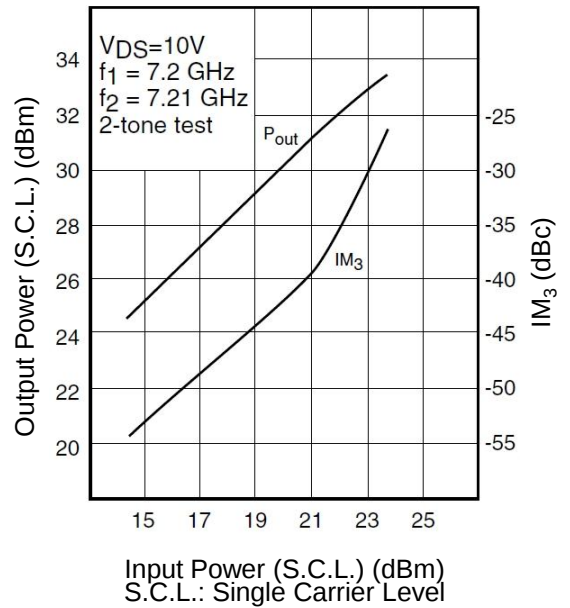
G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

CASE STYLE	IB	
ESD	Class 3A	4000V to 8000V
Note : Based on JEDEC JESD22-A114 (C=100pF, R=1.5kohm)		
RoHS Compliance	Yes	

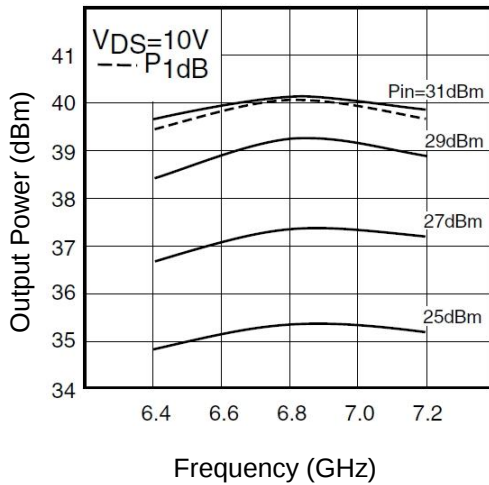
POWER DERATING CURVE



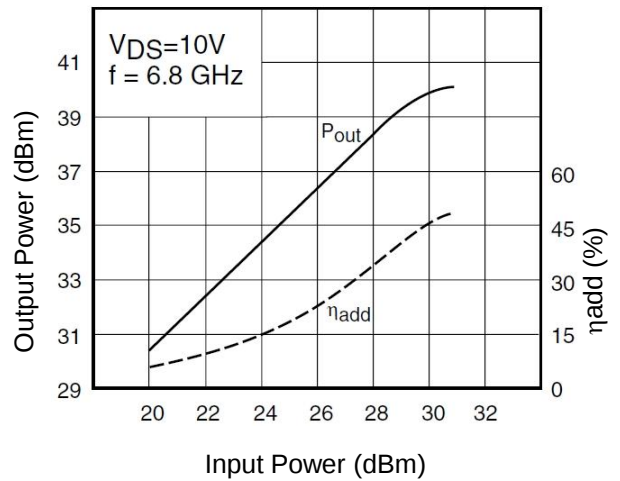
OUTPUT POWER & IM_3 vs. INPUT POWER

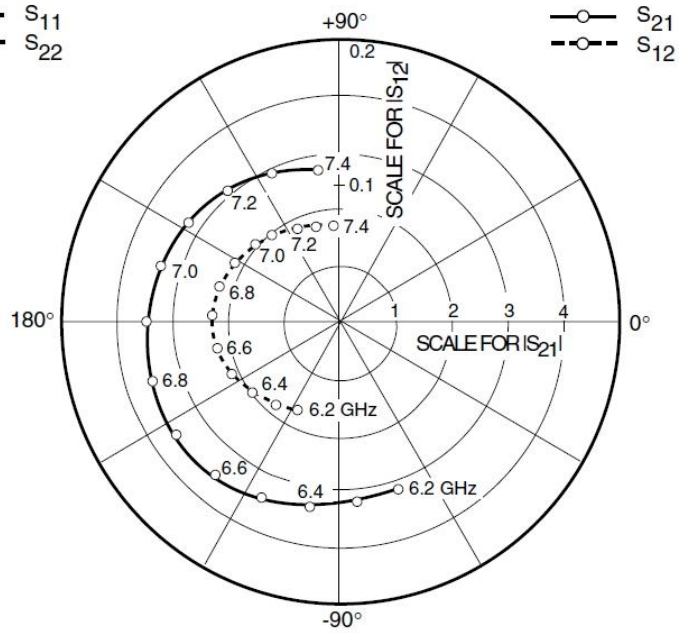
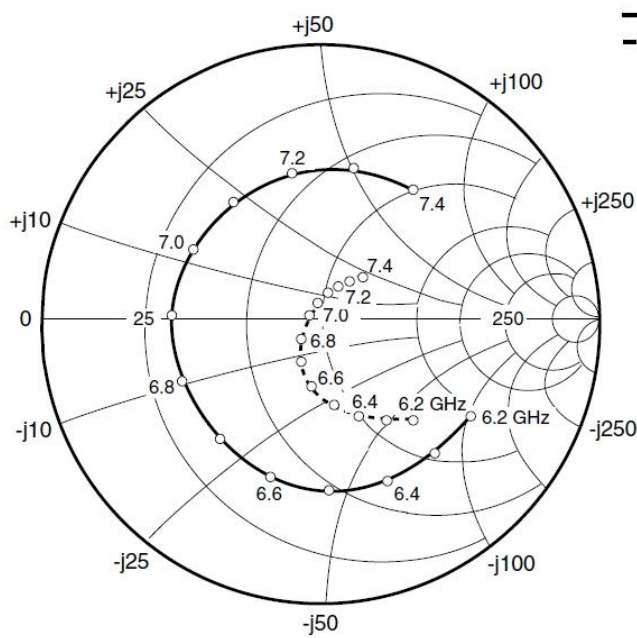


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER



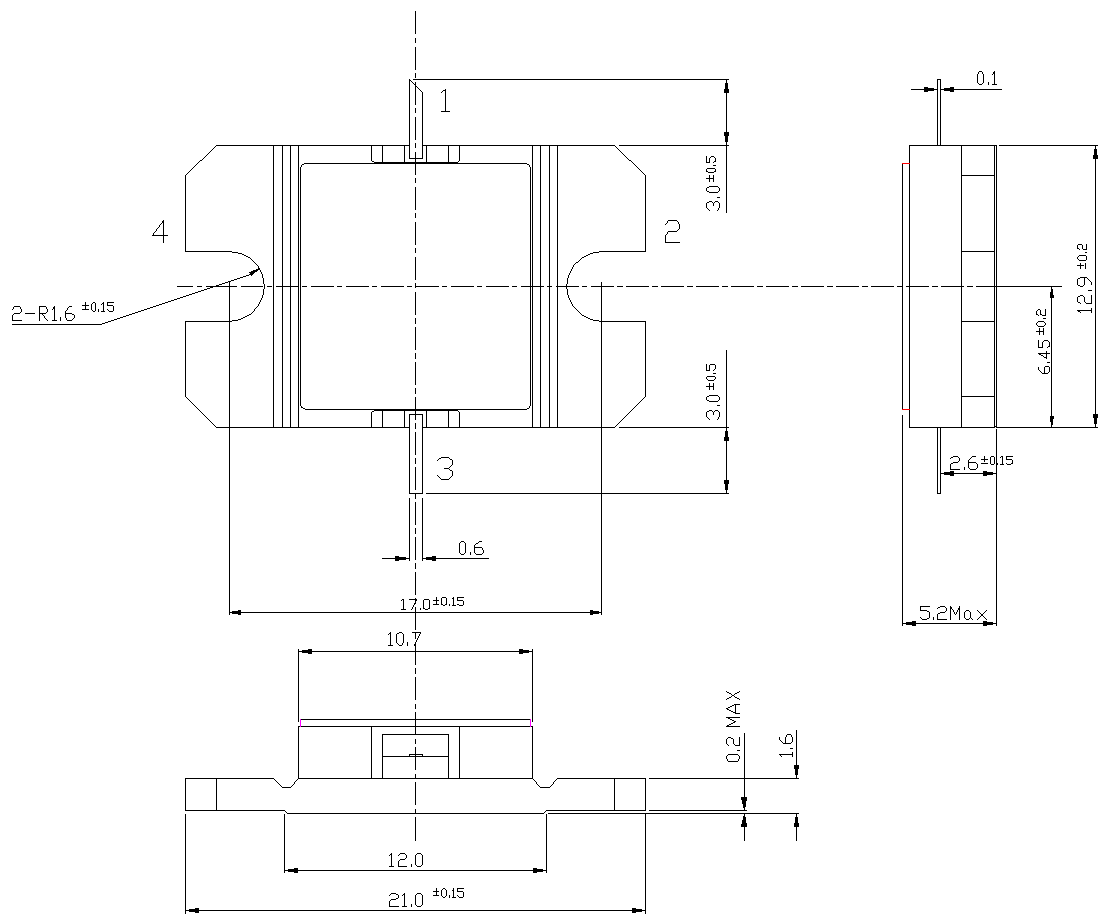


S-PARAMETERS

$V_{DS} = 10V$, $I_{DS} = 2200mA$

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6200	0.633	-32.8	3.131	-71.1	0.072	-118.5	0.481	-47.7
6300	0.629	-49.8	3.194	-85.0	0.077	-129.0	0.429	-57.5
6400	0.619	-67.7	3.314	-99.3	0.082	-141.0	0.372	-68.7
6500	0.605	-87.3	3.403	-114.2	0.088	-153.7	0.305	-81.5
6600	0.588	-108.4	3.495	-129.9	0.091	-167.5	0.234	-96.6
6700	0.567	-131.1	3.541	-146.1	0.093	178.4	0.163	-115.0
6800	0.548	-155.9	3.551	-162.9	0.091	164.7	0.099	-139.7
6900	0.533	177.8	3.500	179.9	0.087	151.1	0.055	169.2
7000	0.530	150.9	3.409	162.8	0.081	138.3	0.063	103.2
7100	0.534	126.4	3.273	147.2	0.077	127.8	0.098	73.6
7200	0.547	101.0	3.113	130.4	0.073	116.4	0.135	60.5
7300	0.562	77.6	2.929	114.5	0.068	105.9	0.173	52.2
7400	0.575	55.2	2.749	98.3	0.067	94.8	0.220	45.4

■ Package Outline
Case Style : IB



Pin Assignment

- 1 : Gate
- 2 : Source
- 3 : Drain
- 4 : Source

Unit : mm

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.